

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

### **IXTP98N075T**

2.70

1.35

6.65

8.86

<ul> <li>100% a</li> <li>Minimuperform</li> <li>APPLI</li> <li>DC/DC</li> <li>High C</li> </ul>	haracterized avalanche voltage ar avalanche tested um Lot-to-Lot variations for robust nance and reliable operation <b>CATION</b> COnverters urrent Switching Applications LUTE MAXIMUM RATINGS(T <sub>a</sub> =2 PARAMETER	device	UNIT	pin 1, Gate 2, Drain 3, Source TO-220C package
V <sub>DSS</sub>	Drain-Source Voltage	75	V	
V <sub>GS</sub>		±20	.,	
VGS	Gate-Source Voltage	±20	V	
VGS ID	Gate-Source Voltage Drain Current-Continuous	98	A	
ID	Drain Current-Continuous	98	A	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $
I <sub>D</sub>	Drain Current-Continuous Drain Current-Single Pulsed	98 280	A	DIM         MIN         MAX           A         15.50         15.90           B         9.90         10.20           C         4.20         4.50           D         0.70         0.90
I <sub>D</sub> I <sub>DM</sub> P <sub>D</sub>	Drain Current-Continuous         Drain Current-Single Pulsed         Total Dissipation @Tc=25°C	98 280 230	A A W	DIM         MIN         MAX           A         15.50         15.90           B         9.90         10.20           C         4.20         4.50

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	0.65	°C/W

R

S

U

v

2.30

1.29

6.45 8.66



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	PARAMETER CONDITIONS		МАХ	UNIT	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	75		V	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 100 μ A	2.0	4.0	V	
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 25A		10	mΩ	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V		±200	nA	
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		2		
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C		150	μA	
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 98A; V <sub>GS</sub> = 0V		1.5	V	

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